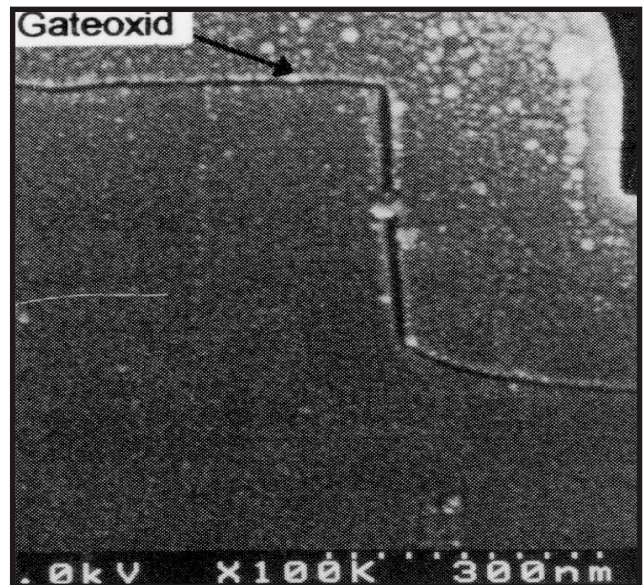
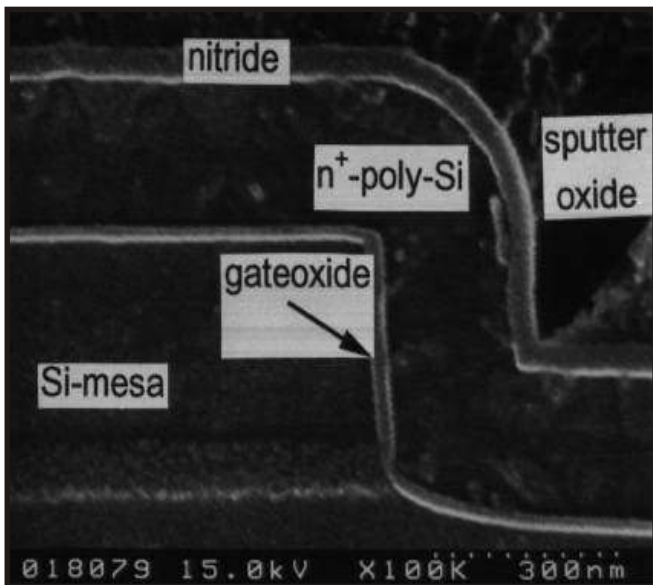


Plasmalab Data

Anisotropic Si RIE for a vertical MOSFET

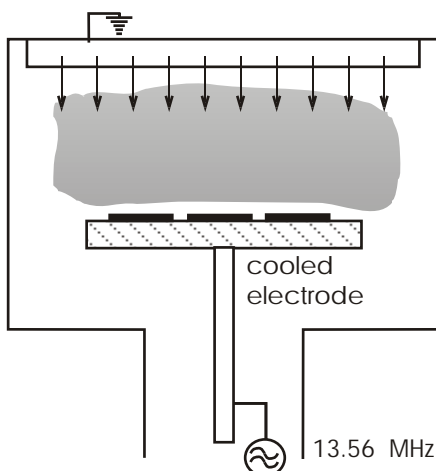


0.3 μm deep, anisotropic F RIE into Si
(etch process: Uni Bochum,
Lehrstuhl für Elektronische Bauelemente
deposition processes: Universität der Bundeswehr,
Institut für Physik, Lehrstuhl für Mikrosystemtechnik
left SEM published in J. of Material Science)



Plasmalab 80 Plus
Plasmalab 800 Plus

Plasmalab System 100
Plasmalab System 133



Technology:

- Reactive Ion Etching
- 13.56 MHz Plasma Excitation
- Fluor based Process
- Parallel Plate Reactor
- Shower Head Gas Inlet

Results:

- Rate : > 25 nm/ min
- Uniformity: <= +/- 4.5 % (4")
- anisotropic etch
- smooth walls